Kl Pey

List of Publications by Year
in descending order

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28	438	8	13
papers	citations	h-index	g-index

1162889

1125617

28	28	28	298
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effect of Copper TSV Annealing on Via Protrusion for TSV Wafer Fabrication. Journal of Electronic Materials, 2012, 41, 2533-2542.	1.0	136
2	The effects of dielectric slots on Copper/Low-k interconnects reliability. , 2009, , .		1
3	Nature of breakdown in ultrathin gate dielectrics. , 2008, , .		0
4	Design for Manufacturability in Backend Reliability and Packaging of Nanoscale Technologies. , 2007, , .		0
5	Improved electrical performance of erbium silicide Schottky diodes formed by Pre-RTA amorphization of Si. IEEE Electron Device Letters, 2006, 27, 93-95.	2.2	9
6	Multiple-pulse laser thermal annealing for the formation of Co-silicided junction. IEEE Electron Device Letters, 2006, 27, 237-239.	2.2	5
7	Percolation resistance evolution during progressive breakdown in narrow MOSFETs. IEEE Electron Device Letters, 2006, 27, 396-398.	2.2	8
8	Investigation of intrinsic dielectric breakdown mechanism in Cu/low-/spl kappa/ interconnect system. IEEE Electron Device Letters, 2006, 27, 234-236.	2.2	4
9	Introduction to the Special Issue on the 2004 IEEE International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA). IEEE Transactions on Device and Materials Reliability, 2005, 5, 167-167.	1.5	0
10	Ni(Pt) alloy silicidation on (100) Si and poly-silicon lines. Thin Solid Films, 2004, 462-463, 137-145.	0.8	10
11	Characterization of the junction leakage of Ti-capped Ni-silicided junctions. Thin Solid Films, 2004, 462-463, 202-208.	0.8	4
12	Gate Dielectric-Breakdown-Induced Microstructural Damage in MOSFETs. IEEE Transactions on Device and Materials Reliability, 2004, 4, 38-45.	1.5	31
13	Evidence for Two Distinct Positive Trapped Charge Components in NBTI Stressed p-MOSFETs Employing Ultrathin CVD Silicon Nitride Gate Dielectric. IEEE Electron Device Letters, 2004, 25, 637-639.	2.2	26
14	Expanded Papers From the 2003 IEEE International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA). IEEE Transactions on Device and Materials Reliability, 2004, 4, 4-4.	1.5	1
15	In situ XRD analysis of Ni(Pt)/Si(100) reactions in low temperature regime â‰¤400Â°C. Solid State Communications, 2003, 128, 325-328.	0.9	8
16	Polarity-dependent dielectric breakdown-induced epitaxy (DBIE) in Si MOSFETs. IEEE Electron Device Letters, 2002, 23, 526-528.	2.2	62
17	Correction to "Polarity-dependent dielectric breakdown-induced epitaxy (DBIE) in Si MOSFETs". IEEE Electron Device Letters, 2002, 23, 676-676.	2.2	0
18	New salicidation technology with Ni(Pt) alloy for MOSFETs. IEEE Electron Device Letters, 2001, 22, 568-570.	2.2	85

#	Article	IF	Citations
19	Low-frequency noise measurement of copper damascene interconnects. , 0, , .		2
20	Stress-induced voiding beneath vias with wide copper metal leads. , 0, , .		6
21	Dielectric-breakdown-induced epitaxy: a universal breakdown defect in ultrathin gate dielectrics. , 0, , .		1
22	Structural analysis of breakdown in ultrathin gate dielectrics using transmission electron microscopy. , 0, , .		1
23	Stress-induced voiding in multi-level copper/low-k interconnects. , 0, , .		11
24	New insight into gate dielectric breakdown induced MOSFET degradation by novel percolation path resistance measurements. , 0, , .		11
25	Novel dielectric slots in Cu interconnects for suppressing stress-induced void failure. , 0, , .		3
26	Study of dielectric-breakdown-induced dopant redistribution based on MOSFET diode I-V measurement. , 0, , .		3
27	Stress migration reliability of wide CU interconnects with gouging vias. , 0, , .		7
28	Exponential dependence of percolation resistance on gate voltage and its impacts on progressive breakdown. , 0, , .		3